

CMLDM8120TG
SURFACE MOUNT SILICON
P-CHANNEL
ENHANCEMENT-MODE
MOSFET



www.centrasemi.com



SOT-563 CASE

DESCRIPTION:

The CENTRAL SEMICONDUCTOR CMLDM8120TG is an enhancement-mode P-Channel MOSFET, manufactured by the P-Channel DMOS Process, designed for high speed pulsed amplifier and driver applications. This MOSFET offers low $r_{DS(ON)}$ and a MAX threshold voltage of 0.85V.

MARKING CODE: CT8

FEATURES:

- Device is **Halogen Free** by design
- Low $r_{DS(ON)}$
- MAX Threshold Voltage (0.85V)
- Logic level compatibility

APPLICATIONS:

- Load/Power switches
- Power supply converter circuits
- Battery powered portable equipment

MAXIMUM RATINGS: ($T_A=25^\circ\text{C}$)

| |
|--|
| Drain-Source Voltage |
| Gate-Source Voltage |
| Continuous Drain Current (Steady State) |
| Continuous Drain Current, $t \leq 5.0\text{s}$ |
| Continuous Source Current (Body Diode) |
| Maximum Pulsed Drain Current, $t_p=10\mu\text{s}$ |
| Maximum Pulsed Source Current, $t_p=10\mu\text{s}$ |
| Power Dissipation (Note 1) |
| Power Dissipation (Note 2) |
| Power Dissipation (Note 3) |
| Operating and Storage Junction Temperature |
| Thermal Resistance |

SYMBOL

| | | |
|----------------|-------------|--------------------|
| V_{DS} | 20 | V |
| V_{GS} | 8.0 | V |
| I_D | 860 | mA |
| I_D | 950 | mA |
| I_S | 360 | mA |
| I_{DM} | 4.0 | A |
| I_{SM} | 4.0 | A |
| P_D | 350 | mW |
| P_D | 300 | mW |
| P_D | 150 | mW |
| T_J, T_{stg} | -65 to +150 | $^\circ\text{C}$ |
| θ_{JA} | 357 | $^\circ\text{C/W}$ |

UNITS

ELECTRICAL CHARACTERISTICS: ($T_A=25^\circ\text{C}$ unless otherwise noted)

| SYMBOL | TEST CONDITIONS | MIN | TYP | MAX | UNITS |
|----------------------|--|------|-------|-------|----------|
| I_{GSSF}, I_{GSSR} | $V_{GS}=8.0\text{V}, V_{DS}=0$ | | 1.0 | 50 | nA |
| I_{DSS} | $V_{DS}=20\text{V}, V_{GS}=0$ | | 5.0 | 500 | nA |
| BV_{DSS} | $V_{GS}=0, I_D=250\mu\text{A}$ | 20 | 24 | | V |
| $V_{GS(th)}$ | $V_{DS}=V_{GS}, I_D=250\mu\text{A}$ | 0.45 | | 0.85 | V |
| V_{SD} | $V_{GS}=0, I_S=360\text{mA}$ | | | 0.9 | V |
| $r_{DS(ON)}$ | $V_{GS}=4.5\text{V}, I_D=0.95\text{A}$ | | 0.085 | 0.15 | Ω |
| $r_{DS(ON)}$ | $V_{GS}=4.5\text{V}, I_D=0.77\text{A}$ | | 0.085 | 0.142 | Ω |
| $r_{DS(ON)}$ | $V_{GS}=2.5\text{V}, I_D=0.67\text{A}$ | | 0.13 | 0.20 | Ω |
| $r_{DS(ON)}$ | $V_{GS}=1.8\text{V}, I_D=0.20\text{A}$ | | 0.19 | 0.24 | Ω |
| $r_{DS(ON)}$ | $V_{GS}=1.2\text{V}, I_D=0.10\text{A}$ | | 0.60 | | Ω |

Notes: (1) Ceramic or aluminum core PC Board with copper mounting pad area of 4.0mm^2
(2) FR-4 Epoxy PC Board with copper mounting pad area of 4.0mm^2
(3) FR-4 Epoxy PC Board with copper mounting pad area of 1.4mm^2

R4 (8-June 2015)

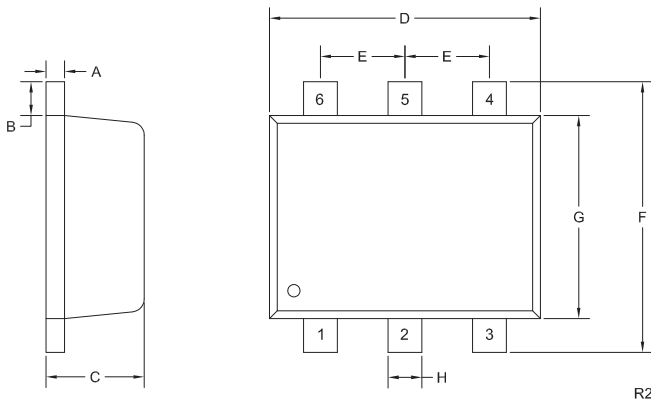
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ELECTRICAL CHARACTERISTICS - Continued: ($T_A=25^\circ\text{C}$ unless otherwise noted)

| SYMBOL | TEST CONDITIONS | MIN | TYP | MAX | UNITS |
|--------------|---|-----|------|-----|-------|
| g_{FS} | $V_{DS}=10\text{V}$, $I_D=0.81\text{A}$ | 2.0 | | | S |
| C_{rss} | $V_{DS}=16\text{V}$, $V_{GS}=0$, $f=1.0\text{MHz}$ | | 80 | | pF |
| C_{iss} | $V_{DS}=16\text{V}$, $V_{GS}=0$, $f=1.0\text{MHz}$ | | 200 | | pF |
| C_{oss} | $V_{DS}=16\text{V}$, $V_{GS}=0$, $f=1.0\text{MHz}$ | | 60 | | pF |
| $Q_{g(tot)}$ | $V_{DS}=10\text{V}$, $V_{GS}=4.5\text{V}$, $I_D=1.0\text{A}$ | | 3.56 | | nC |
| Q_{gs} | $V_{DS}=10\text{V}$, $V_{GS}=4.5\text{V}$, $I_D=1.0\text{A}$ | | 0.36 | | nC |
| Q_{gd} | $V_{DS}=10\text{V}$, $V_{GS}=4.5\text{V}$, $I_D=1.0\text{A}$ | | 1.52 | | nC |
| t_{on} | $V_{DD}=10\text{V}$, $V_{GS}=4.5\text{V}$, $I_D=0.95\text{A}$, $R_G=6\Omega$ | | 20 | | ns |
| t_{off} | $V_{DD}=10\text{V}$, $V_{GS}=4.5\text{V}$, $I_D=0.95\text{A}$, $R_G=6\Omega$ | | 25 | | ns |

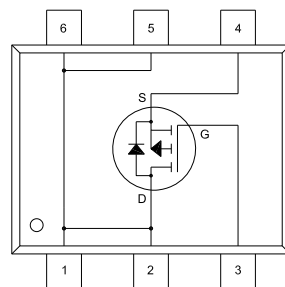
SOT-563 CASE - MECHANICAL OUTLINE



| SYMBOL | DIMENSIONS | | | |
|--------|------------|-------|-------------|------|
| | INCHES | | MILLIMETERS | |
| | MIN | MAX | MIN | MAX |
| A | 0.0027 | 0.007 | 0.07 | 0.18 |
| B | 0.008 | | 0.20 | |
| C | 0.017 | 0.024 | 0.45 | 0.60 |
| D | 0.059 | 0.067 | 1.50 | 1.70 |
| E | 0.020 | | 0.50 | |
| F | 0.059 | 0.067 | 1.50 | 1.70 |
| G | 0.043 | 0.051 | 1.10 | 1.30 |
| H | 0.006 | 0.012 | 0.15 | 0.30 |

SOT-563 (REV: R2)

PIN CONFIGURATION



LEAD CODE:

- 1) Drain
- 2) Drain
- 3) Gate
- 4) Source
- 5) Drain
- 6) Drain

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R4 (8-June 2015)

OUTSTANDING SUPPORT AND SUPERIOR SERVICES



PRODUCT SUPPORT

Central's operations team provides the highest level of support to insure product is delivered on-time.

- Supply management (Customer portals)
- Inventory bonding
- Consolidated shipping options
- Custom bar coding for shipments
- Custom product packing

DESIGNER SUPPORT/SERVICES

Central's applications engineering team is ready to discuss your design challenges. Just ask.

- Free quick ship samples (2nd day air)
- Online technical data and parametric search
- SPICE models
- Custom electrical curves
- Environmental regulation compliance
- Customer specific screening
- Up-screening capabilities
- Special wafer diffusions
- PbSn plating options
- Package details
- Application notes
- Application and design sample kits
- Custom product and package development

REQUESTING PRODUCT PLATING

1. If requesting Tin/Lead plated devices, add the suffix "TIN/LEAD" to the part number when ordering (example: 2N2222A TIN/LEAD).
2. If requesting Lead (Pb) Free plated devices, add the suffix "PBFREE" to the part number when ordering (example: 2N2222A PBFREE).

CONTACT US

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